

RLS245

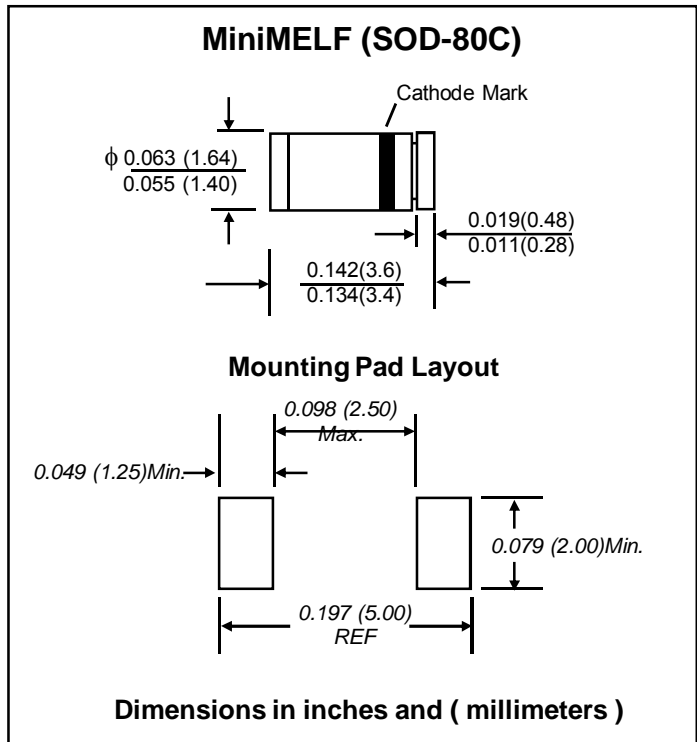
HIGH SPEED SWITCHING DIODE

FEATURES :

- * Silicon Epitaxial Planar Diode
- * High Voltage Switching
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

Case: MiniMELF Glass Case (SOD-80)
Weight: approx. 0.05g



Absolute Maximum Ratings (Ta = 25 °C)

| Parameter | Symbol | Value | Unit |
|----------------------------|-------------|--------------|------|
| Peak Reverse Voltage | V_{RM} | 250 | V |
| DC Reverse Voltage | V_R | 220 | V |
| Peak Forward Current | I_{FM} | 625 | mA |
| Average Forward Current | $I_{F(AV)}$ | 200 | mA |
| Surge Forward Current (1s) | I_{SURGE} | 1000 | mA |
| Power Dissipation | P_D | 300 | mW |
| Junction Temperature | T_J | 175 | °C |
| Storage Temperature Range | T_{STG} | -65 to + 175 | °C |

Electrical Characteristics (Ta = 25 °C)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|-------------------------------|----------|---|------|------|------|---------|
| Reverse Current | I_R | $V_R = 220 V$ | - | - | 10 | μA |
| Forward Voltage | V_F | $I_F = 200 mA$ | - | - | 1.5 | V |
| Capacitance between terminals | C_T | $f = 1MHz ; V_R = 0 V$ | - | - | 3 | pF |
| Reverse Recovery Time | T_{rr} | $I_F = 20 mA ; I_R = 20mA,$ $R_L = 50\Omega$ | - | - | 75 | ns |

RATING AND CHARACTERISTIC CURVES (RLS245)

FIG.1 - REVERSE RECOVERY TIME (T_{rr}) MEASUREMENT CIRCUIT

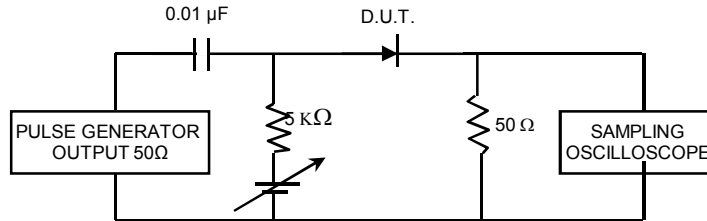


FIG.2 - FORWARD CHARACTERISTICS

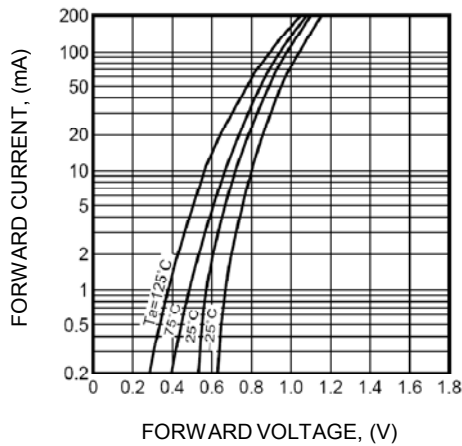


FIG.3 - REVERSE CHARACTERISTICS

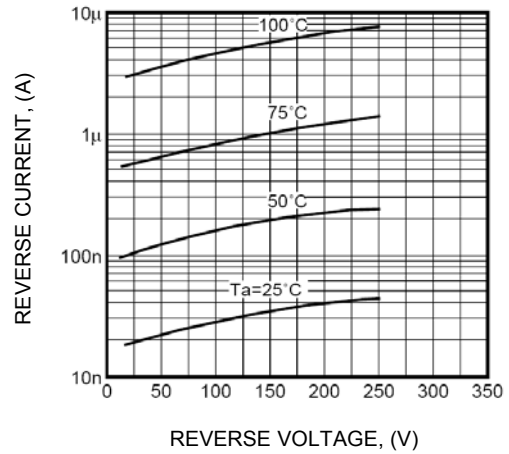


FIG.4 - SURGE CURRENT CHARACTERISTICS

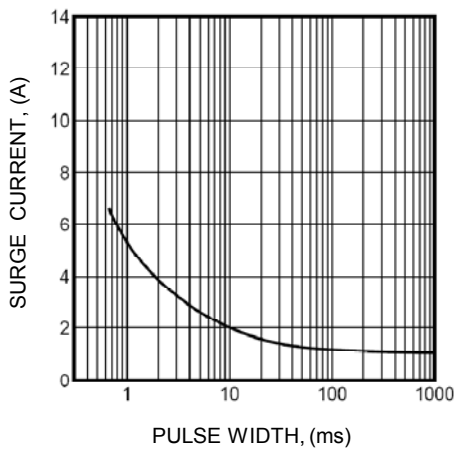


FIG.5 - CAPACITANCE BETWEEN TERMINALS CHARACTERISTICS

